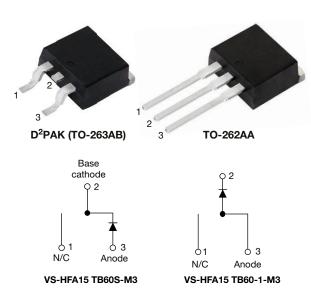


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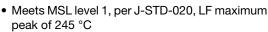
HEXFRED®, Ultrafast Soft Recovery Diode, 15 A



PRIMARY CHARACTERISTICS						
I _{F(AV)}	15 A					
V _R	600 V					
V _F at I _F	1.2 V					
t _{rr} (typ.)	23 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB), TO-262AA					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}





- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA15TB60S, VS-HFA15TB60-1 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60S. VS-HFA15TB60-1 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and sizes. The HEXFRED VS-HFA15TB60S, VS-HFA15TB60-1 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current	I _F	T _C = 100 °C	15				
Single pulse forward current	I _{FSM}		150	Α			
Maximum repetitive forward current	I _{FRM}		60				
Maximum navva dissination	Б	T _C = 25 °C	74	W			
Maximum power dissipation	P _D	T _C = 100 °C	29				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			



Series inductance

 L_{S}

VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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8.0

nΗ

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-		
		I _F = 15 A		-	1.3	1.7	V	
Maximum forward voltage	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0		
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6		
Maximum reverse	,	V _R = V _R rated	Coo fig. 0	-	1.0	10		
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 ^{\circ}\text{X} V_R \text{ rated}$	See fig. 2	-	400	1000	μA	
Junction capacitance	Ст	$V_{\rm P} = 200 \text{ V}$	See fig. 3	_	25	50	рF	

Measured lead to lead 5 mm from package body

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CON	IDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	Vμs, V _R = 30 V	-	23	-		
Reverse recovery time See fig. 5	t _{rr1}	T _J = 25 °C		-	50	60	ns	
Geo lig. o	t _{rr2}	T _J = 125 °C		-	105	120		
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 200 V	-	4.5	6.0	- A	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	84	180		
See fig. 7	Q _{rr2}	T _J = 125 °C		-	241	600	TIC	
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7		
Thermal resistance, junction-to-ambient	R _{thJA}	R _{thJA} Typical socket mount		-	80	K/W	
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveigni			-	0.07	-	OZ.	
Marking device		Case style D ² PAK (TO-263AB)	HFA15TB60S				
Marking device		Case style TO-262AA	HFA15TB60-1				



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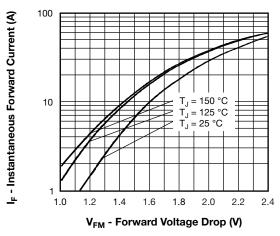


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

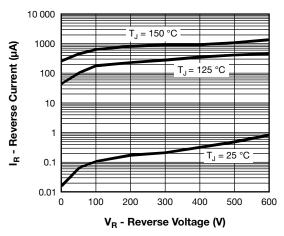


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

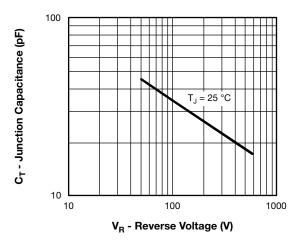


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

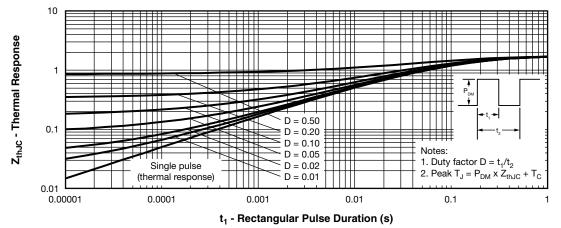


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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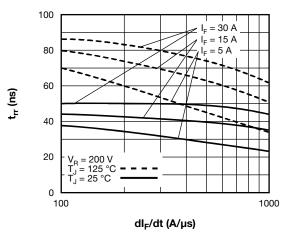


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

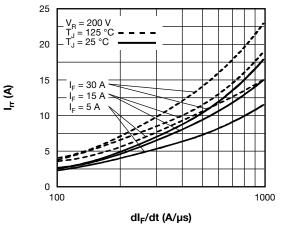


Fig. 6 - Typical Recovery Current vs. dl_F/dt

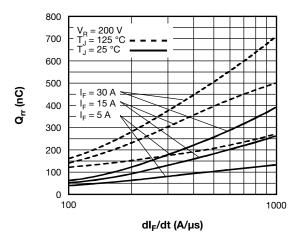


Fig. 7 - Typical Stored Charge vs. dl_F/dt

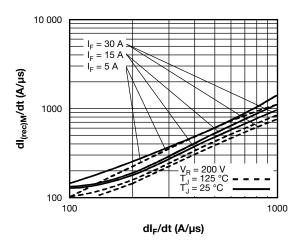
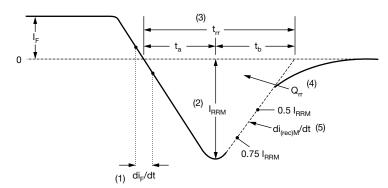


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_r$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

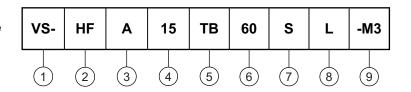
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- HEXFRED® family

3 - Electron irradiated

Current rating (15 = 15 A)

Fackage: TB = TO-220

6 - Voltage rating (60 = 600 V)

• -1 = TO-262AA

None = tube (50 pieces)

• L = tape and reel (left oriented, for D2PAK (TO-263AB) package)

• R = tape and reel (right oriented, for D²PAK (TO-263AB) package)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE OR TAPE AND REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA15TB60S-M3	50	1000	Antistatic plastic tube				
VS-HFA15TB60SL-M3	800	800	13" diameter reel				
VS-HFA15TB60SR-M3	800	800	13" diameter reel				
VS-HFA15TB60-1-M3	50	1000	Antistatic plastic tube				

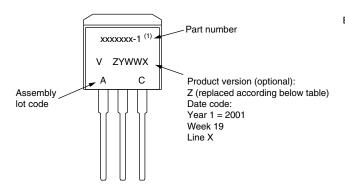
LINKS TO RELATED DOCUMENTS						
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164				
Differsions	TO-262AA	www.vishay.com/doc?96165				
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information		www.vishay.com/doc?96424				
SPICE model		www.vishay.com/doc?95357				



Part Marking Information

Vishay Semiconductors

TO-262



Example: This is a xxxxxxx-1 ⁽¹⁾ with assembly lot code AC, assembled on WW 19, 2001

in the assembly line "X"

Note

(1) If part number contain "H" as last digit, product is AEC-Q101 qualified

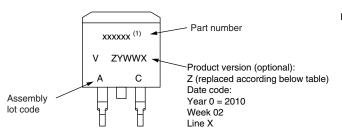
ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION			
A	Termination lead (Pb)-free			
В	Totally lead (Pb)-free			
E	RoHS-compliant and termination lead (Pb)-free			
F	RoHS-compliant and totally lead (Pb)-free			
М	Halogen-free, RoHS-compliant and termination lead (Pb)-free			
N	Halogen-free, RoHS-compliant and totally lead (Pb)-free			
G	Green			



Part Marking Information

Vishay Semiconductors

D²PAK



Example: This is a xxxxxx ⁽¹⁾ with assembly lot code AC, assembled on WW 02, 2010

Note

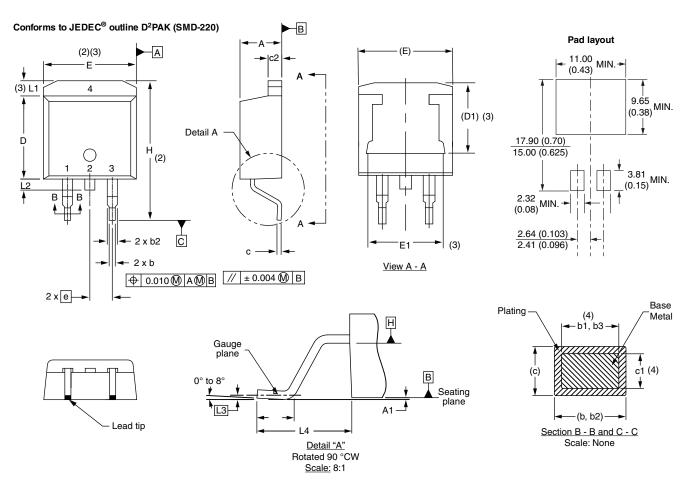
(1) If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION		
А	Termination lead (Pb)-free		
В	Totally lead (Pb)-free		
E	RoHS-compliant and termination lead (Pb)-free		
F	RoHS-compliant and totally lead (Pb)-free		
M	Halogen-free, RoHS-compliant, and termination lead (Pb)-free		
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free		
G Green			



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

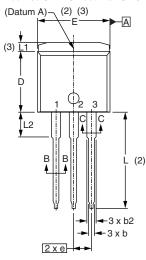
Revision: 13-Jul-17 Document Number: 96164

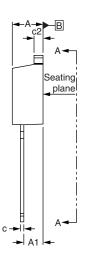


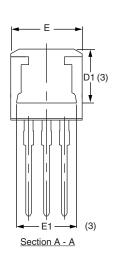
TO-262AA

DIMENSIONS in millimeters and inches

Modified JEDEC® outline TO-262







⊕ 0.010 **M** A**M** B

Lead assignments

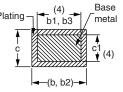


Diodes

1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

			1		
SYMBOL	MILLIN	IETERS	INC	HES	NOTES
3.MB0L	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

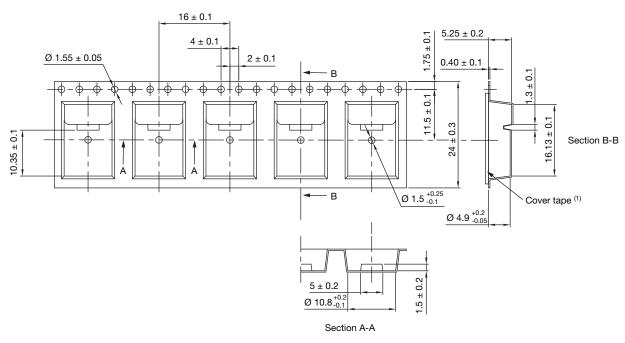
⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

D²PAK (TO-263AB)

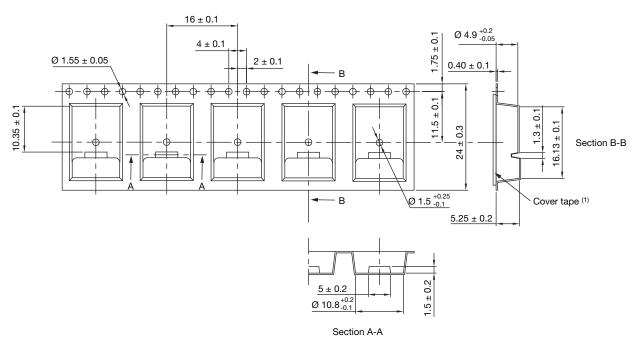
CARRIER TAPE FOR TAPE AND REEL LEFT in millimeters



Note

(1) For dimensions, see next pages

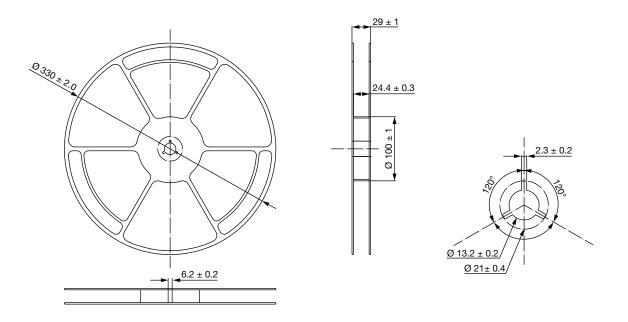
CARRIER TAPE FOR TAPE AND REEL RIGHT in millimeters



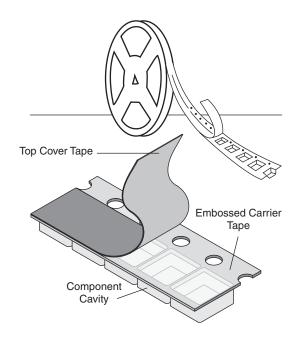
Note

(1) For dimensions, see next pages

REEL FOR CARRIER TAPE in millimeters



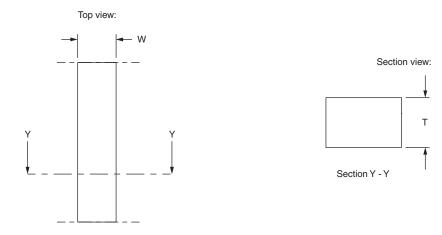
CARRIER TAPE AND REEL PACKAGING D²PAK (TO-263AB)



Packaging Information

Vishay Semiconductors

COVER TAPE FOR CARRIER TAPE in millimeters



APPLICATION	COVER TAPE WIDTH W	COVER TAPE THICKNESS T	CARRIER TAPE WIDTH	MATERIAL
D ² PAK (TO-263AB)	21.3 ± 0.1	0.060 ± 0.01	24	Antistatic/treated/transparent/polyester



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Vishay

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